

First Named Inventor	Scott Derner
Serial No.	10/017,658
Filing Date	December 12, 2002
Group Art Unit	2818
Examiner Name	Tan Nguyen
Facsimile No.	703-308-7724
Attorney Docket No.	400.105US01

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Title: HALF DENSITY ROM EMBEDDED DRAM

**Total Pages: 7 (including transmittal sheet)**

Commissioner for Patents  
Washington, D.C. 20231

**Enclosures**

The following documents are enclosed:

**FAX RECEIVED**X An Amendment and Response to Office Action of January 15, 2003 (6 pgs.).

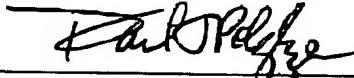
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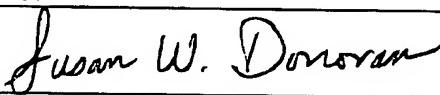
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I certify that this paper, and the above-identified documents, are being transmitted by facsimile to Group 2818 at the United States Patent and Trademark Office on April 15, 2003.

Name	Susan W. Donovan	Signature	
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S/N 10/017,658

PATENT

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

First Named

Inventor: Scott Dernier

Examiner: Tan Nguyen

Serial No.: 10/017,658

Group Art Unit: 2818

Filed: December 12, 2001

Atty. Docket No.: 400.105US01

Title: HALF DENSITY ROM EMBEDDED DRAM

8/03  
JMK/Key  
4-18-03

**AMENDMENT AND RESPONSE**

Commissioner for Patents  
Washington, D.C. 20231

In response to the Office Action dated January 15, 2003, please amend the above-identified patent application as follows:

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**IN THE CLAIMS**

1. (Original) A memory device comprising:  
a read only memory (ROM) cell hard programmed to a first data state;  
a dynamic memory cell; and  
access circuitry to couple the ROM cell and the dynamic memory cell to differential digit lines.
2. (Original) The memory device of claim 1 wherein the access circuitry comprises:  
a first transistor coupled between the ROM cell and a first digit line; and  
a second transistor coupled between the dynamic memory cell and a second digit line,  
wherein gate connections of the first and second transistors are coupled to different word lines.
3. (Original) The memory device of claim 1 wherein the ROM cell is hard programmed to Vcc.
4. (Original) The memory device of claim 1 wherein the ROM cell is hard programmed to Vss.

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